



THE DATASHEET OF BCP5616TA



SOT223 NPN SILICON PLAIN MEDIUM POWER TRANSISTOR

ISSUE 3 – AUGUST 1995

FEATURES

- * Suitable for AF drivers and output stages
- * High collector current and Low $V_{CE(s)}$

COMPLEMENTARY TYPE – BCP53

PARTMARKING DETAILS – BCP56
BCP56 – 16
BCP56 – 16

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$
Operating and Storage Temperature Range



ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	10
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	
Static Forward Current Transfer Ratio	h_{FE}	40 25 BCP56-10 63 BCP56-16 10
Transition Frequency	f_T	

*Measured under pulsed conditions. Pulse

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View BCP5616TA on WIN SOURCE](#)
-  [Diodes Incorporated Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management